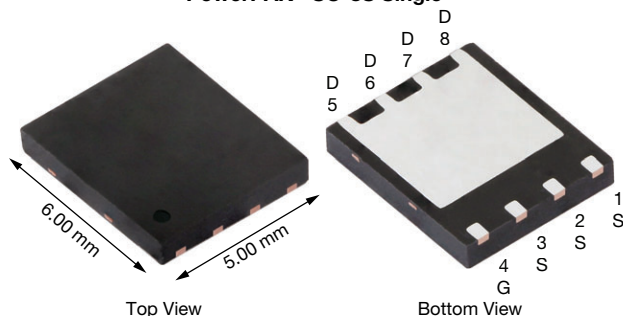


# N-Channel 150 V (D-S) MOSFET

**PowerPAK® SO-8S Single**


## FEATURES

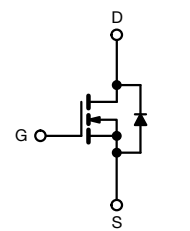
- TrenchFET® Gen V power MOSFET
- Very low  $R_{DS(on)}$  x  $Q_g$  figure-of-merit (FOM)
- Leadership  $R_{DS(on)}$  minimizes power loss from conduction
- 100 %  $R_g$  and UIS tested
- Enhance power dissipation and lower  $R_{thJC}$
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
FREE

## APPLICATIONS

- Synchronous rectification
- DC/DC converters
- OR-ing and hot swap switch
- Power supplies
- Motor drive control
- Battery management



N-Channel MOSFET

## PRODUCT SUMMARY

$V_{DS}$ (V)	150
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.0056
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5$ V	0.0062
$Q_g$ typ. (nC)	55
$I_D$ (A) <sup>a</sup>	144
Configuration	Single

## ORDERING INFORMATION

Package	PowerPAK SO-8S
Lead (Pb)-free and halogen-free	SiRS5700DP-T1-RE3

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	150	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	144
		$T_C = 70$ °C	115
		$T_A = 25$ °C	25 <sup>b, c</sup>
		$T_A = 70$ °C	20 <sup>b, c</sup>
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	300	A
Continuous source-drain diode current	$I_S$	$T_C = 25$ °C	252
		$T_A = 25$ °C	7.6 <sup>b, c</sup>
Single pulse avalanche current	$I_{AS}$	37	
Single pulse avalanche energy	$E_{AS}$	68	mJ
Maximum power dissipation	$P_D$	$T_C = 25$ °C	278
		$T_C = 70$ °C	178
		$T_A = 25$ °C	8.3 <sup>b, c</sup>
		$T_A = 70$ °C	5.3 <sup>b, c</sup>
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>c</sup>		260	

## THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	$R_{thJA}$	10	15	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	0.3	0.45	

### Notes

- $T_C = 25$  °C
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK SO-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 45 °C/W



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	150	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 10 mA	-	100	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	-7.5	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	-	4	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	10	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.0046	0.0056	Ω
		V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 20 A	-	0.0048	0.0062	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 35 A	-	122	-	S
Dynamic <sup>b</sup>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	5455	-	pF
Output capacitance	C <sub>oss</sub>		-	480	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	10	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	73	110	nC
Gate-source charge	Q <sub>gs</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 20 A	-	55	83	
Gate-drain charge	Q <sub>gd</sub>		-	25	-	
Output charge	Q <sub>oss</sub>		-	7.6	-	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V	-	160	-	Ω
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.28	1.4	2.8	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 75 V, R <sub>L</sub> = 7.5 Ω, I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	20	40	ns
Rise time	t <sub>r</sub>		-	15	30	
Turn-off delay time	t <sub>d(off)</sub>		-	40	80	
Fall time	t <sub>f</sub>		-	25	50	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 75 V, R <sub>L</sub> = 7.5 Ω, I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 7.5 V, R <sub>g</sub> = 1 Ω	-	25	50	
Rise time	t <sub>r</sub>		-	21	40	
Turn-off delay time	t <sub>d(off)</sub>		-	40	80	
Fall time	t <sub>f</sub>		-	25	50	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	252	A
Pulse diode forward current	I <sub>SM</sub>		-	-	300	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.75	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	95	190	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	310	620	nC
Reverse recovery fall time	t <sub>a</sub>		-	64	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	31	-	

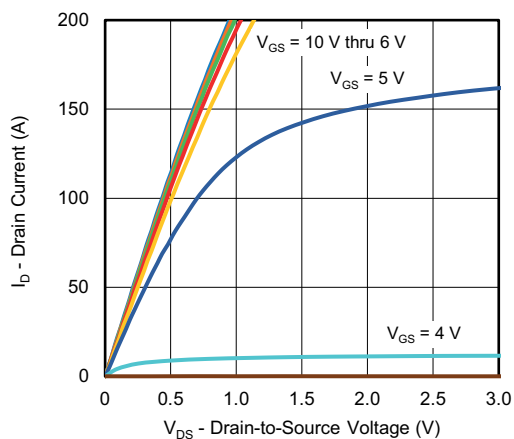
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

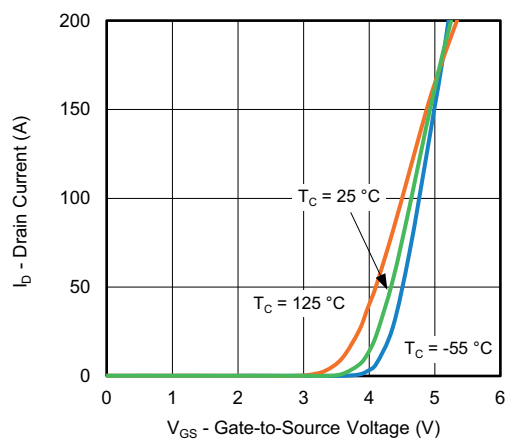
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



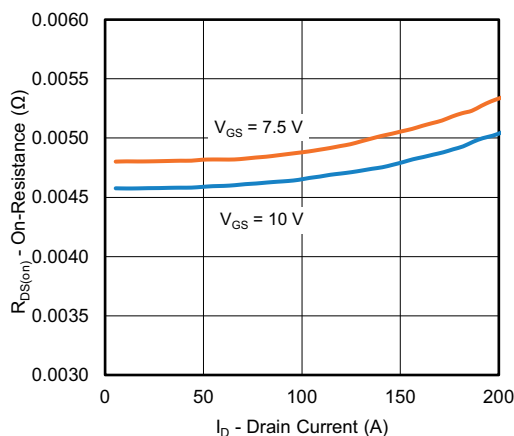
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



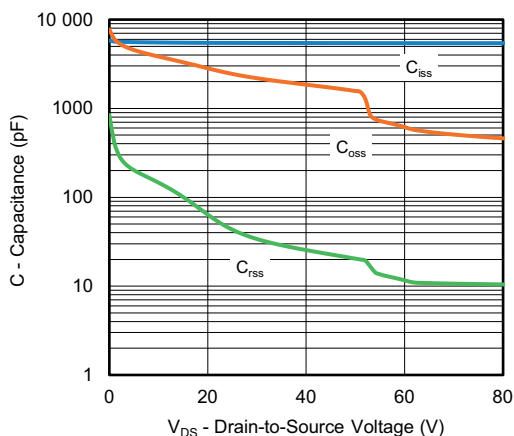
**Output Characteristics**



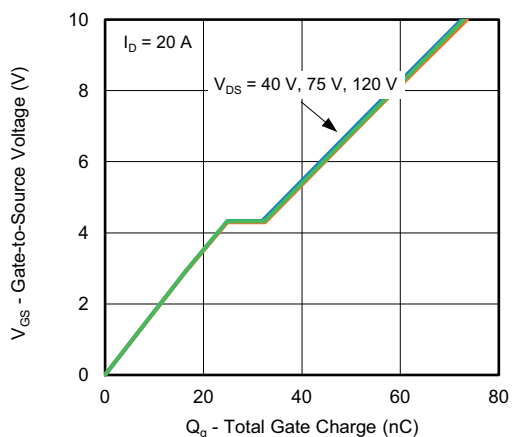
**Transfer Characteristics**



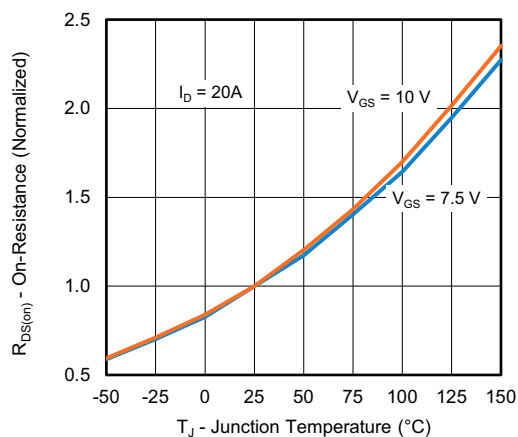
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



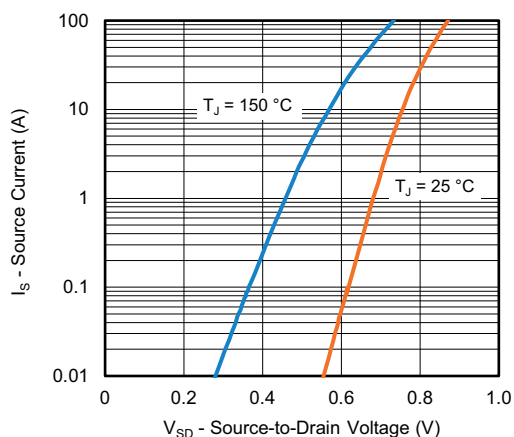
**Gate Charge**



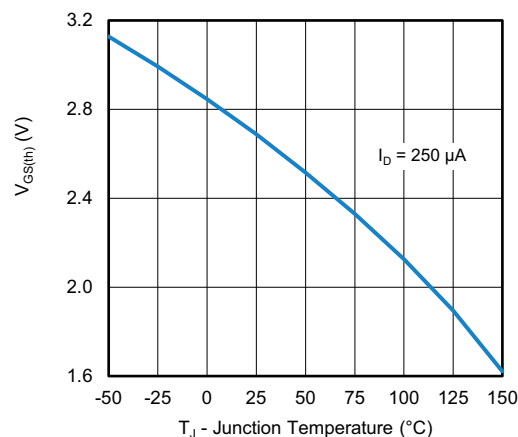
**On-Resistance vs. Junction Temperature**



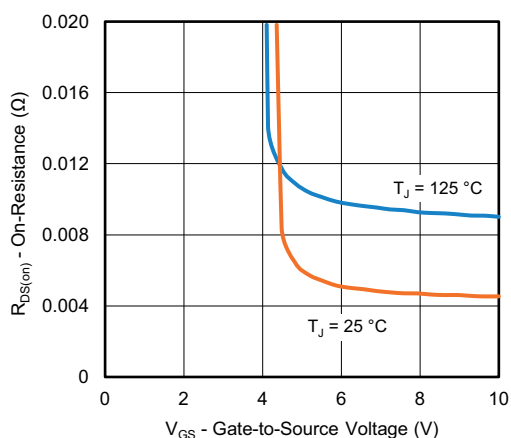
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



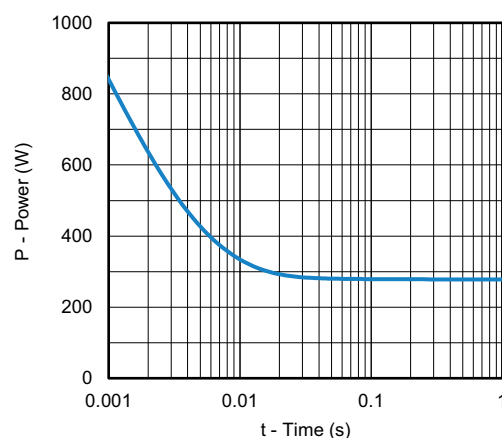
**Source-Drain Diode Forward Voltage**



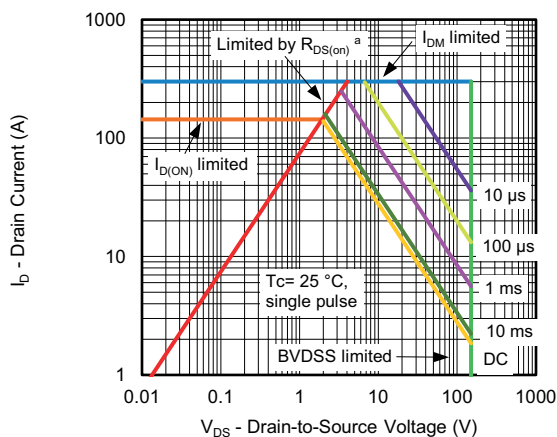
**Threshold Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**Single Pulse Power, Junction-to-Case**



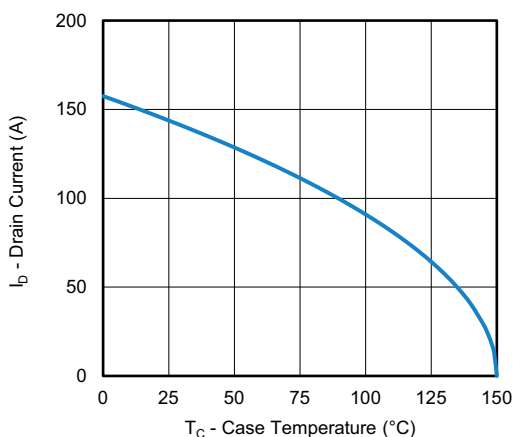
**Safe Operating Area, Junction-to-Case**

**Note**

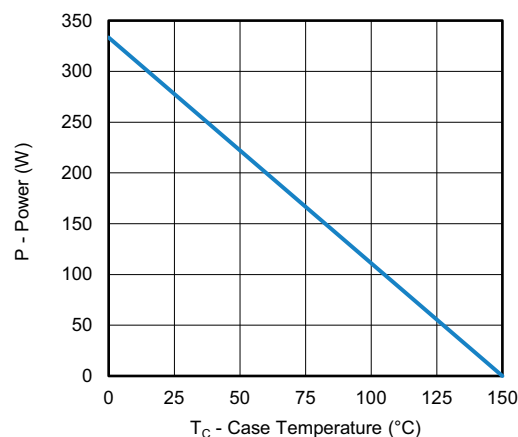
a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



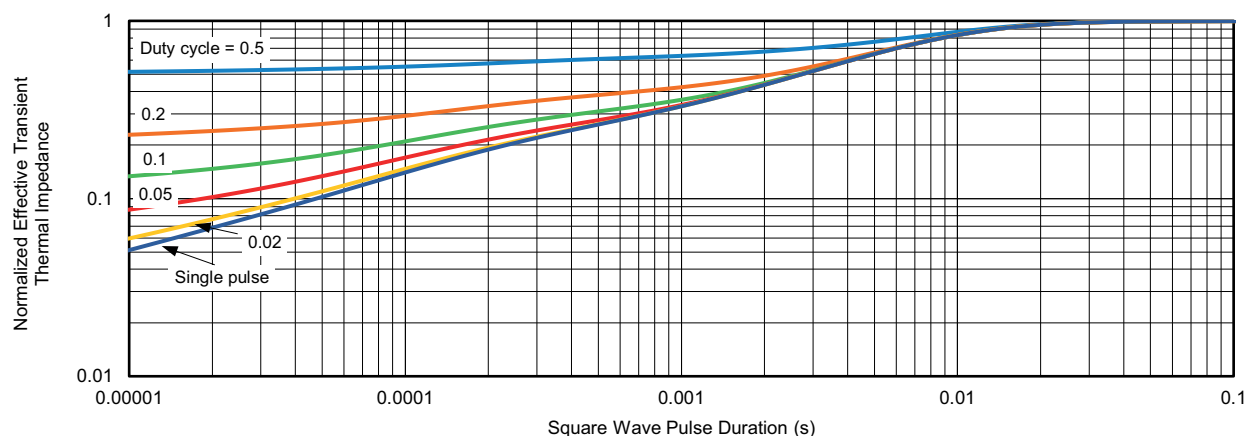
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



**Power, Junction-to-Case**



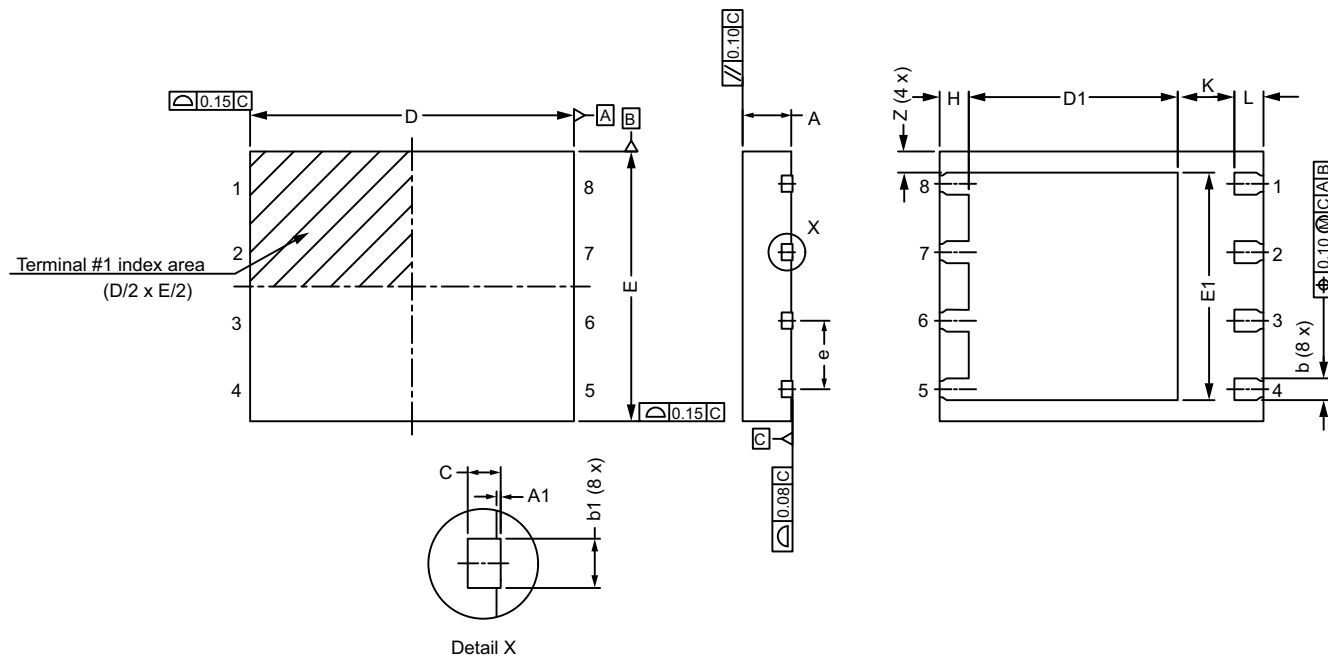
**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- a. The power dissipation  $P_D$  is based on  $T_J \text{ max.} = 150^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

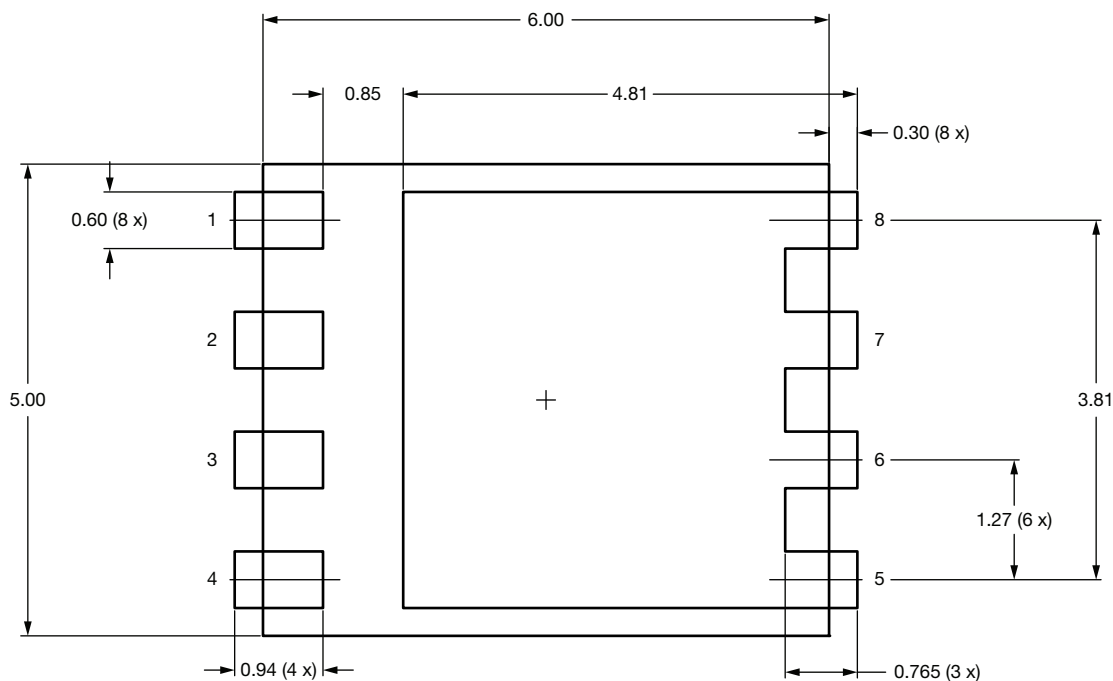
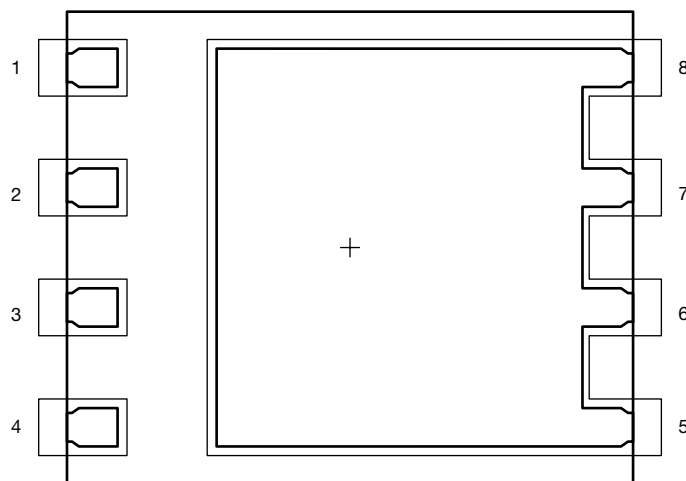


# PowerPAK® SO-8S BWL



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.85	0.90	0.95	0.033	0.035	0.037
A1	-	-	0.05	-	-	0.002
b	0.31	0.41	0.51	0.012	0.016	0.020
b1	0.20	0.30	0.40	0.008	0.012	0.016
c	0.20 ref.			0.008 ref.		
D	5.90	6.00	6.10	0.232	0.236	0.240
D1	3.78	3.88	3.98	0.149	0.153	0.157
E	4.90	5.00	5.10	0.193	0.197	0.201
E1	4.12	4.22	4.32	0.162	0.166	0.170
e	1.27 BSC			0.050 BSC		
H	0.44	0.54	0.64	0.017	0.021	0.025
K	1.05 ref.			0.041 ref.		
L	0.44	0.54	0.64	0.017	0.021	0.025
Z	0.39 ref.			0.015 ref.		
ECN: C20-0936-Rev. A, 03-Aug-2020						
DWG: 6082						

# Recommended Land Pattern PowerPAK® SO-8S BWL





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